

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



November 2013

SGP10N60RUFD 600 V, 10 A Short Circuit Rated IGBT

General Description

Fairchild's RUFD series of Insulated Gate Bipolar Transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, Uninterrupted Power Supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Features

- 10 A, 600 V, T_C = 100°C
- Low Saturation Voltage: V_{CE}(sat) = 2.1 V @ I_C = 10 A
- High Speed Switching
- · High Input Impedance
- · Short Circuit Rating

Applications

Motor Control, UPS, General Inverter





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
	Collector Current	@ T _C = 25°C	16	Α
I _C	Collector Current	@ T _C = 100°C	10	Α
I _{CM (1)}	Pulsed Collector Current		30	Α
	Diode Continuous Forward Current	@ T _C = 25°C	24	Α
lF	Diode Continuous Forward Current	@ T _C = 100°C	12	Α
I _{FM}	Diode Maximum Forward Current		92	Α
T _{SC}	Short Circuit Withstand Time	@ T _C = 100°C	10	us
P _D	Maximum Power Dissipation	@ T _C = 25°C	75	W
	Maximum Power Dissipation	@ T _C = 100°C	30	W
T _J	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Secon	ds	300	°C

Notes: (1) Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case		1.6	°C/W
$R_{\theta JC}(DIODE)$	Thermal Resistance, Junction-to-Case		2.5	°C/W
R _{0,JA}	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

Electrical Characteristics	of the IGBT	T _C = 25°C unless otherwise noted
-----------------------------------	-------------	--

Symbol	Parameter Test Conditions		Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \text{ uA}$	600			V
$\frac{\Delta B_{VCES}}{\Delta T_{J}}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_C = 1 \text{ mA}$		0.6		V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0 V			250	uA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$			± 100	nΑ
On Chai	racteristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 10 \text{ mA}, V_{CE} = V_{GE}$	5.0	6.0	8.5	V
	Collector to Emitter	$I_C = 10 \text{ A}, V_{GE} = 15 \text{ V}$		2.2	2.8	V
V _{CE(sat)}	Saturation Voltage	I _C = 16 A, V _{GE} = 15 V		2.5		V
Dynami	c Characteristics					
C _{ies}	Input Capacitance	V 20 V V 0 V		660		pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz		115		pF
C _{res}	Reverse Transfer Capacitance	1 = 1 1011 12		25		рF
Switchir	ng Characteristics					
t _{d(on)}	Turn-On Delay Time			15		ns
t _r	Rise Time			30		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_{C} = 10 \text{ A},$		36	50	ns
t _f	Fall Time	$R_G = 20 \Omega, V_{GE} = 15 V,$		158	200	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C		141		uJ
E _{off}	Turn-Off Switching Loss			215		uJ
E _{ts}	Total Switching Loss			356	500	uJ
t _{d(on)}	Turn-On Delay Time			16		ns
t _r	Rise Time			33		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_{C} = 10 \text{ A},$		42	60	ns
t _f	Fall Time	$R_G = 20 \Omega, V_{GE} = 15 V,$		242	350	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 125°C		161		uJ
E _{off}	Turn-Off Switching Loss			452		uJ
E _{ts}	Total Switching Loss			613	860	uJ
T _{sc}	Short Circuit Withstand Time	$V_{CC} = 300 \text{ V}, V_{GE} = 15 \text{ V}$ @ $T_{C} = 100^{\circ}\text{C}$	10			us
Q_g	Total Gate Charge	$V_{CE} = 300 \text{ V}, I_{C} = 10 \text{ A},$		30	45	nC
Q_{ge}	Gate-Emitter Charge	$V_{CE} = 300 \text{ V}, I_{C} = 10 \text{ A},$ $V_{GE} = 15 \text{ V}$		5	10	nC
Q _{gc}	Gate-Collector Charge	*GE = 10 *		8	16	nC
L _e	Internal Emitter Inductance	Measured 5mm from PKG		7.5		nΗ

Electrical Characteristics of DIODE $T_{C} = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
V _{FM} Diode Forward Voltage	Diada Farward Valtage	I 10 A	$T_C = 25^{\circ}C$		1.4	1.7	V
	I _F = 12 A	T _C = 100°C		1.3		V	
+	t _{rr} Diode Reverse Recovery Time		$T_C = 25^{\circ}C$		42	60	ns
^L rr			T _C = 100°C		60		115
1	Diode Peak Reverse Recovery	I _F = 12 A,	$T_C = 25^{\circ}C$		3.5	6.0	Α
ırr	Current	$di_F/dt = 200 A/\mu s$	T _C = 100°C		5.6		_ ^
Q _{rr} Diode Re	Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$		80	180	nC
			$T_C = 100$ °C		220		10

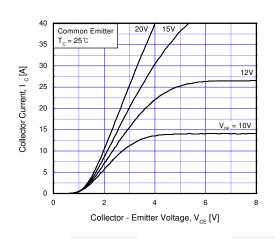


Fig 1. Typical Output Characteristics

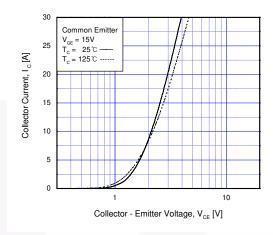


Fig 2. Typical Saturation Voltage Characteristics

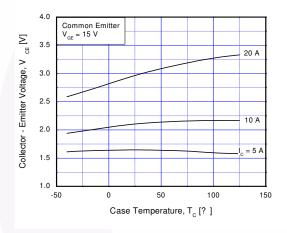


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

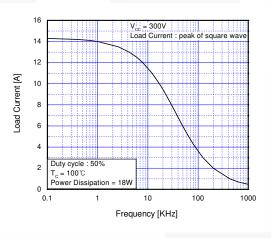


Fig 4. Load Current vs. Frequency

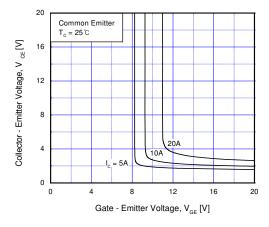


Fig 5. Saturation Voltage vs. V_{GE}

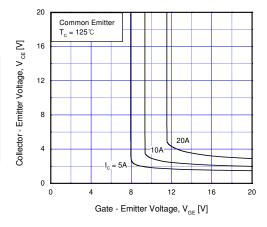


Fig 6. Saturation Voltage vs. V_{GE}

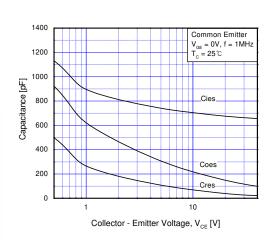


Fig 7. Capacitance Characteristics

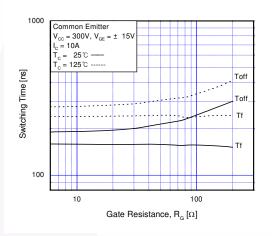


Fig 9. Turn-Off Characteristics vs.
Gate Resistance

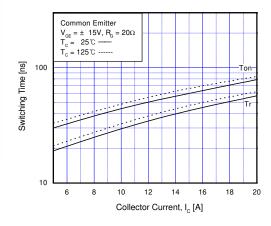


Fig 11. Turn-On Characteristics vs. Collector Current

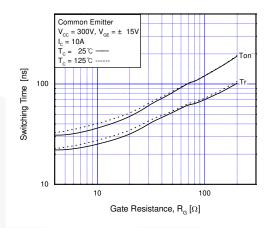


Fig 8. Turn-On Characteristics vs.
Gate Resistance

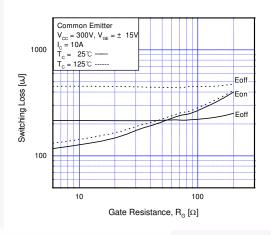


Fig 10. Switching Loss vs. Gate Resistance

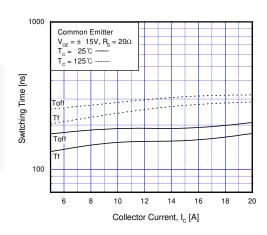


Fig 12. Turn-Off Characteristics vs. Collector Current

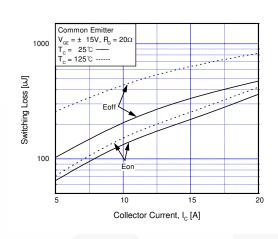


Fig 13. Switching Loss vs. Collector Current

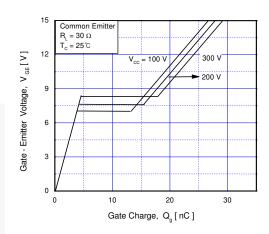


Fig 14. Gate Charge Characteristics

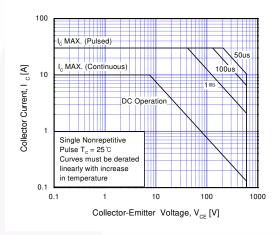


Fig 15. SOA Characteristics

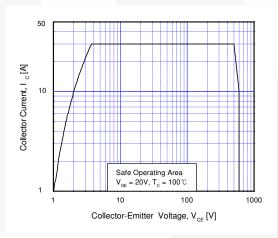


Fig 16. Turn-Off SOA Characteristics

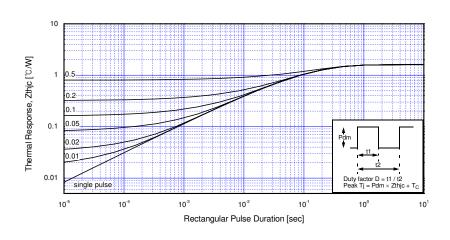


Fig 17. Transient Thermal Impedance of IGBT

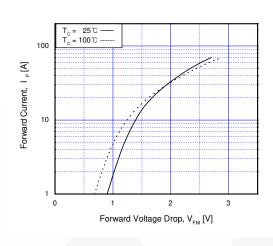


Fig 18. Forward Characteristics

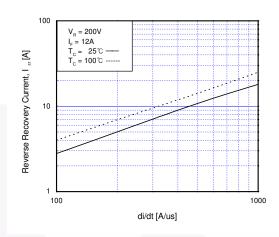


Fig 19. Reverse Recovery Current

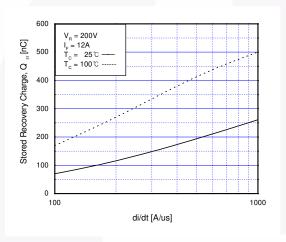


Fig 20. Stored Charge

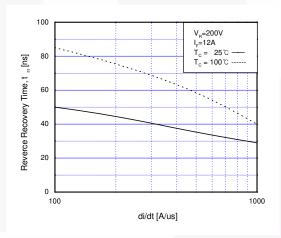


Fig 21. Reverse Recovery Time

Mechanical Dimensions

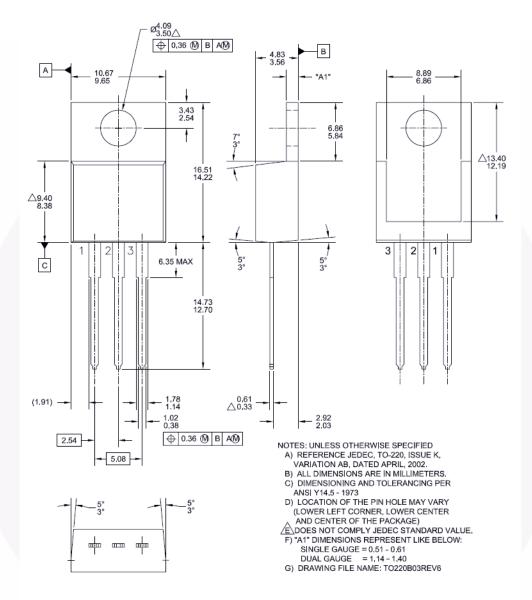


Figure 22. TO-220 3L - TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ AX-CAF BitSiC™ Build it Now™ CorePLUS™ CorePOWER™

CROSSVOLT™ CTL™ Current Transfer Logic™ DEUXPEED® Dual Cool™ EcoSPARK® EfficentMax™ **ESBC™**

Fairchild[®] Fairchild Semiconductor® FACT Quiet Series™ FACT®

FAST® FastvCore™ FETBench™ FPS™

F-PESTM FRFET®

Global Power ResourceSM GreenBridge™

Green FPŠ™ Green FPS™ e-Series™

G*max*™ GTO™ IntelliMAX™ ISOPLANAR™

Marking Small Speakers Sound Louder

MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ mWSaver[®] OptoHiT™ OPTOLOGIC®

OPTOPLANAR®

® PowerTrench® PowerXS™ Programmable Active Droop™

QFĔT

QSTM Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™

Sync-Lock™ SYSTEM®' **TinyBoost** TinyBuck[®] TinyCalc™ TinyLogic[®] TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®* μSerDes™

UHC® Ultra FRFET™ UniFET™ **VCX™** VisualMax™ VoltagePlus™ XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICYFAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their

parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification Product Status		Definition			
Advance Information Formative / In Design		Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Preliminary First Production		Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
No Identification Needed Full Production		Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.			
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.			

Rev. 166

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hol

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative